

ABSTRACT OF THE DISCLOSURE

An electro-magnetic device, such as magnetic memory device, is disclosed that includes means for structuring, attenuating or eliminating stray fields at the boundaries that produce an offset in the magneto-resistive response. The device comprises a conductive first layer and the attenuating means comprises a sink layer, electro-magnetically coupled to the first layer, to attenuate the stray boundary magneto-resistive offset at a boundary of the first layer during electrical operation.

H:\FILES\20000\20353\20353-App.doc